

L469SURKSGW HYPER RED
 SUPER BRIGHT GREEN

Features

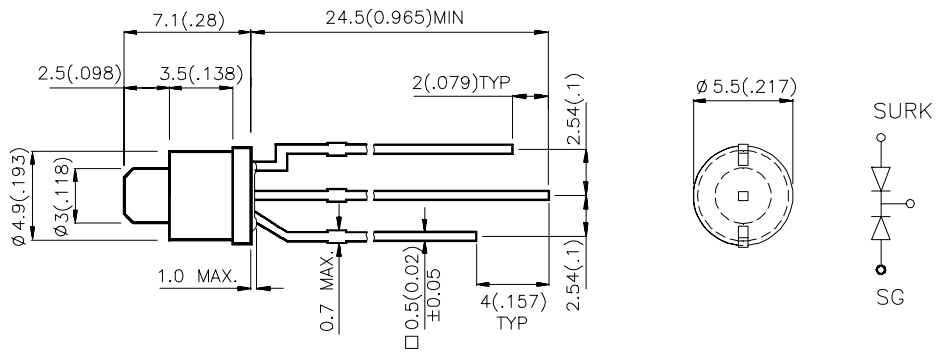
- TWO CHIPS IN SERIES CONNECTION.
- I.C. COMPATIBLE.
- RELIABLE AND RUGGED.
- LONG LIFE - SOLID STATE RELIABILITY.

Description

The Hyper Red source color devices are made with DH InGaAlP on GaAs substrate Light Emitting Diode.

The Super Bright Green source color devices are made with Gallium Phosphide Green Light Emitting Diode.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Selection Guide

Part No.	Dice	Lens Type	Iv (mcd) @ 20mA		Viewing Angle
			Min.	Typ.	2θ1/2
L469SURKSGW	HYPER RED (InGaAlP)	WHITE DIFFUSED	300	600	60°
	SUPER BRIGHT GREEN (GaP)		30	50	

Note:

1. θ1/2 is the angle from optical centerline where the luminous intensity is 1/2 the optical centerline value.

Electrical / Optical Characteristics at T_A=25°C

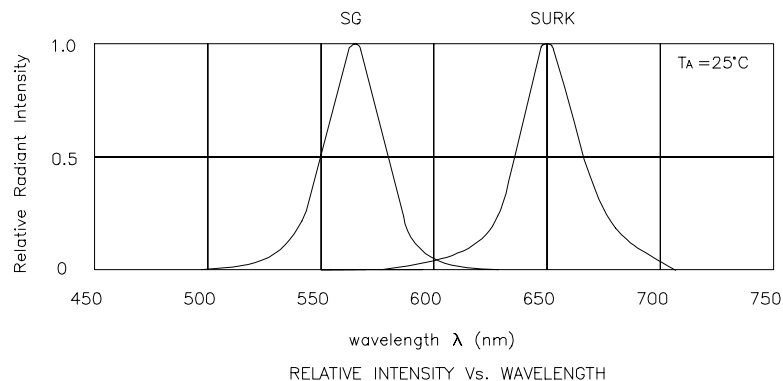
Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ _{peak}	Peak Wavelength	Hyper Red Super Bright Green	650 565		nm	I _F =20mA
λ _D	Dominate Wavelength	Hyper Red Super Bright Green	635 568		nm	I _F =20mA
Δλ _{1/2}	Spectral Line Half-width	Hyper Red Super Bright Green	28 30		nm	I _F =20mA
C	Capacitance	Hyper Red Super Bright Green	35 15		pF	V _F =0V;f=1MHz
V _F	Forward Voltage	Hyper Red Super Bright Green	1.95 2.2	2.5 2.5	V	I _F =20mA
I _R	Reverse Current	All		10	uA	V _R = 5V

Absolute Maximum Ratings at T_A=25°C

Parameter	Hyper Red	Super Bright Green	Units
Power dissipation	170	105	mW
DC Forward Current	30	25	mA
Peak Forward Current [1]	185	140	mA
Operating/Storage Temperature	-40°C To +85°C		
Lead Soldering Temperature[2]	260°C For 5 Seconds		

Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.
2. 4mm below package base.



Hyper Red / Super Bright Green L469SURKSGW

